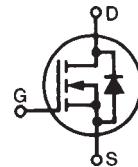


PolarHT™ Power MOSFET

**IXTK 82N25P
IXTQ 82N25P
IXTT 82N25P**

**$V_{DSS} = 250 \text{ V}$
 $I_{D25} = 82 \text{ A}$
 $R_{DS(on)} \leq 35 \text{ m}\Omega$**

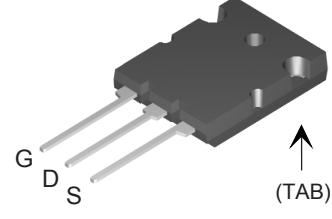
N-Channel Enhancement Mode
Avalanche Rated



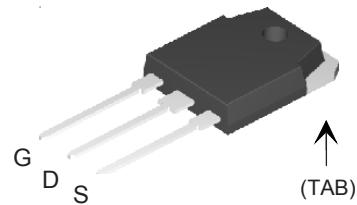
Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	250	V	
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	250	V	
V_{GSS}	Continuous	± 20	V	
V_{GSM}	Transient	± 30	V	
I_{D25}	$T_c = 25^\circ\text{C}$	82	A	
$I_{D(RMS)}$	External lead current limit	75	A	
I_{DM}	$T_c = 25^\circ\text{C}$, pulse width limited by T_{JM}	200	A	
I_{AR}	$T_c = 25^\circ\text{C}$	60	A	
E_{AR}	$T_c = 25^\circ\text{C}$	40	mJ	
E_{AS}	$T_c = 25^\circ\text{C}$	1.0	J	
dv/dt	$I_s \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 4 \Omega$	10	V/ns	
P_D	$T_c = 25^\circ\text{C}$	500	W	
T_J		-55 ... +150	$^\circ\text{C}$	
T_{JM}		150	$^\circ\text{C}$	
T_{stg}		-55 ... +150	$^\circ\text{C}$	
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$	
T_{SOLD}	Plastic body for 10 s	260	$^\circ\text{C}$	
M_d	Mounting torque (TO-3P, TO-264)	1.13/10	Nm/lb.in.	
Weight	TO-3P TO-264 TO-268	5.5 10 5.0	g g g	

Symbol	Test Conditions	Characteristic Values		
	($T_J = 25^\circ\text{C}$, unless otherwise specified)	Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	250		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2.5		5.0 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$		± 100	nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$		25 250	μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$		35	$\text{m}\Omega$

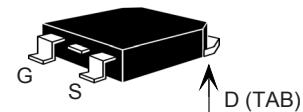
TO-264 (IXTK)



TO-3P (IXTQ)



TO-268 (IXTT)



G = Gate
S = Source

D = Drain
TAB = Drain

Features

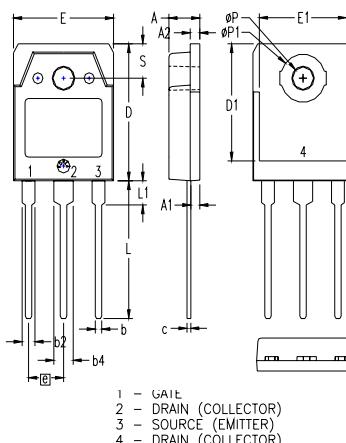
- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

Symbol **Test Conditions**
Characteristic Values
 $(T_J = 25^\circ C, \text{ unless otherwise specified})$

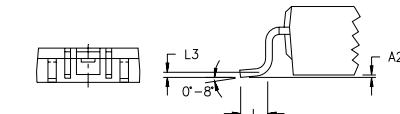
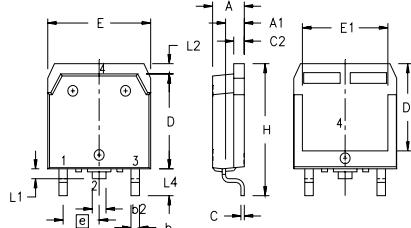
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10 \text{ V}; I_D = 0.5 I_{D25}, \text{ pulse test}$	30	52	S
C_{iss}		4800	pF	
C_{oss}		900	pF	
C_{rss}		210	pF	
$t_{d(on)}$		29	ns	
t_r		20	ns	
$t_{d(off)}$		78	ns	
t_f		22	ns	
$Q_{g(on)}$		142	nC	
Q_{gs}		32	nC	
Q_{gd}		74	nC	
R_{thJC}			0.25 $^\circ\text{C}/\text{W}$	
R_{thCS}	TO-3P	0.21	$^\circ\text{C}/\text{W}$	
	TO-264	0.15	$^\circ\text{C}/\text{W}$	

TO-3P (IXTQ) Outline


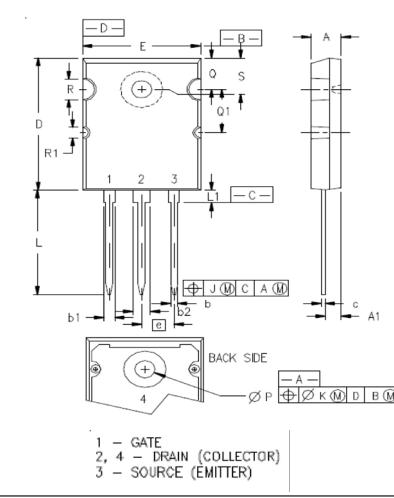
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
$\emptyset P$.126	.134	3.20	3.40
$\emptyset P1$.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

Source-Drain Diode
Characteristic Values
 $(T_J = 25^\circ C, \text{ unless otherwise specified})$

	Test Conditions	Min.	Typ.	Max.
I_s	$V_{GS} = 0 \text{ V}$			82 A
I_{SM}	Repetitive			250 A
V_{SD}	$I_F = I_s, V_{GS} = 0 \text{ V},$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			1.5 V
Q_{RM}	$I_F = 25 \text{ A}, -di/dt = 100 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}, V_{GS} = 0 \text{ V}$	200	ns	
		2.0	μC	

TO-268 (IXTT) Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

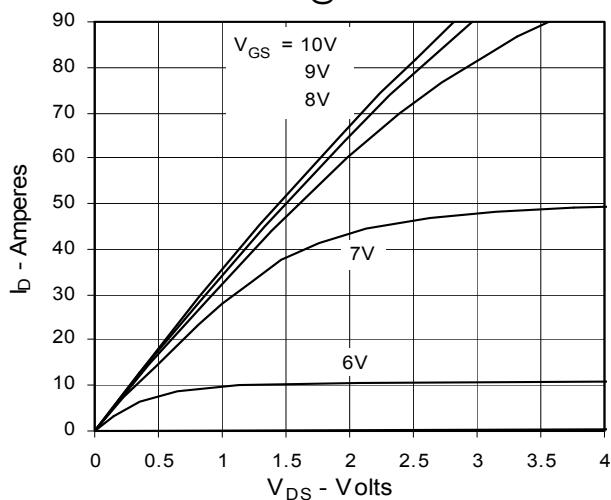
TO-264 (IXTK) Outline


IXYS reserves the right to change limits, test conditions, and dimensions.

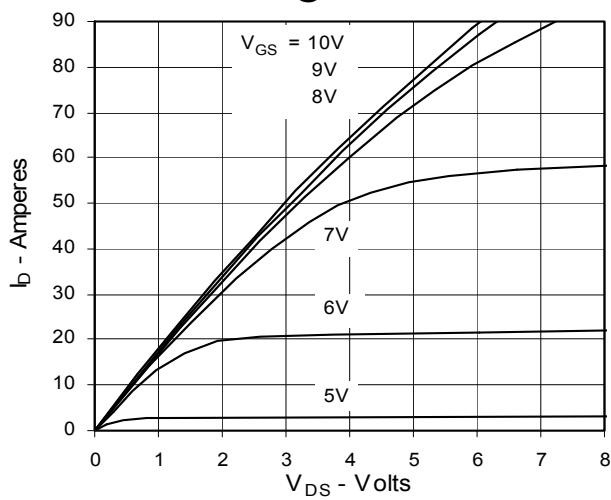
IXYS MOSFETs and IGBTs are covered by 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505

6,683,344 6,727,585 6,710,405B2 6,759,692 6,710,463 6,771,478 B2

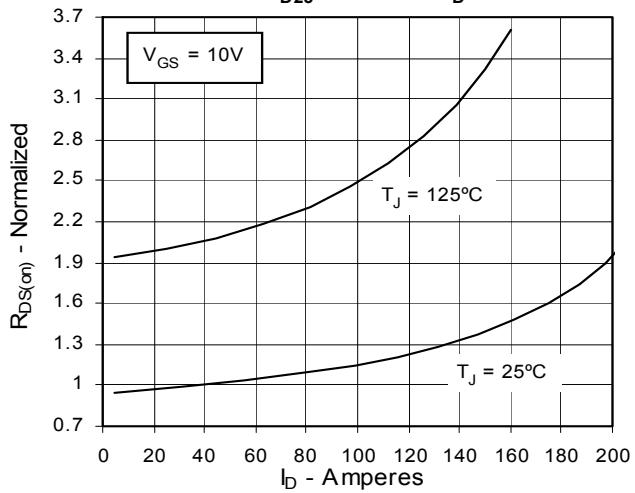
**Fig. 1. Output Characteristics
@ 25°C**



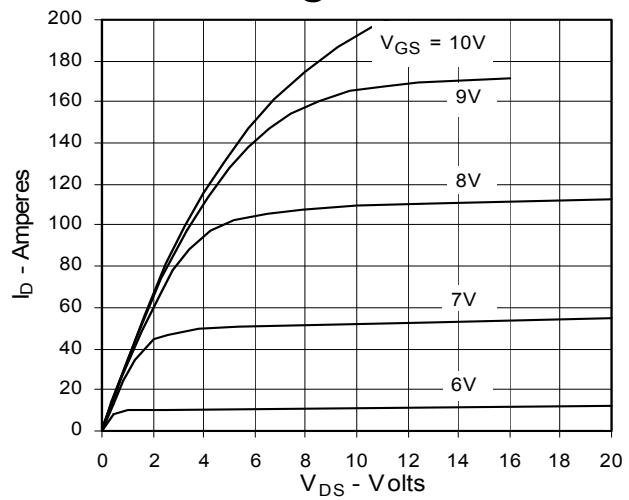
**Fig. 3. Output Characteristics
@ 125°C**



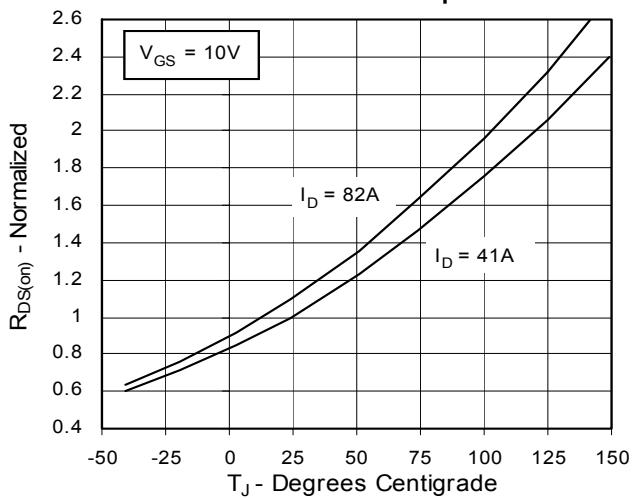
**Fig. 5. $R_{DS(on)}$ Normalized to
0.5 I_{D25} Value vs. I_D**



**Fig. 2. Extended Output Characteristics
@ 25°C**



**Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25}
Value vs. Junction Temperature**



**Fig. 6. Drain Current vs. Case
Temperature**

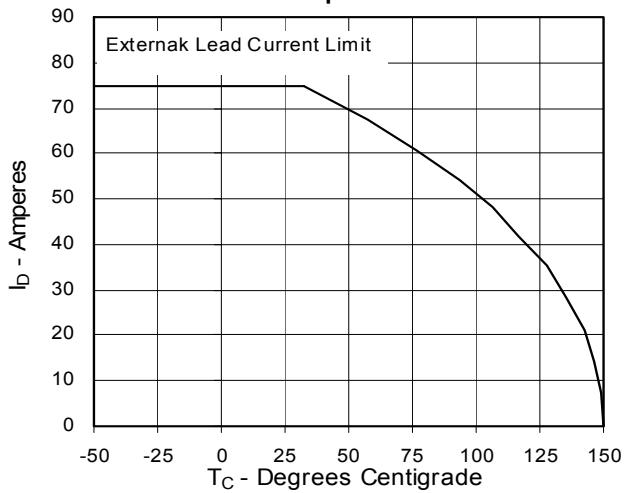


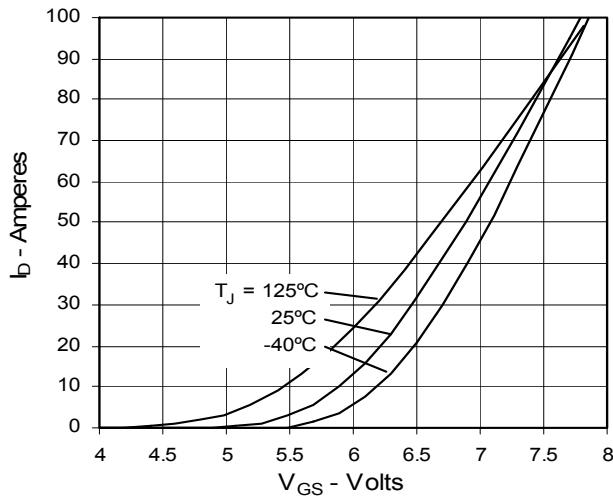
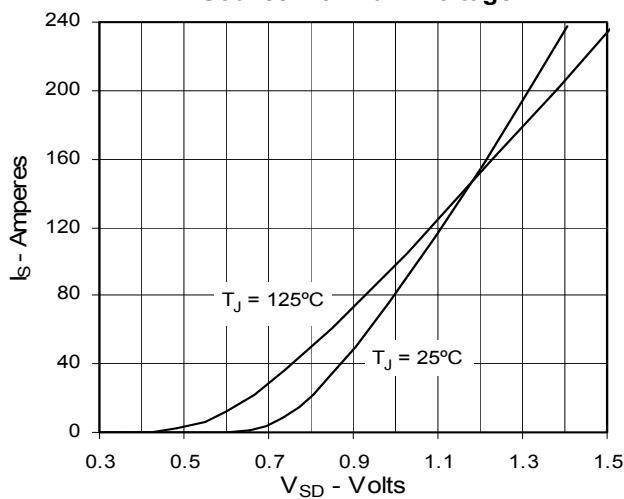
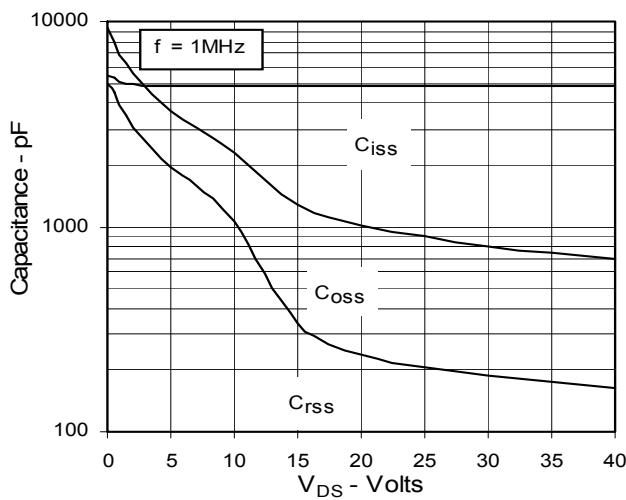
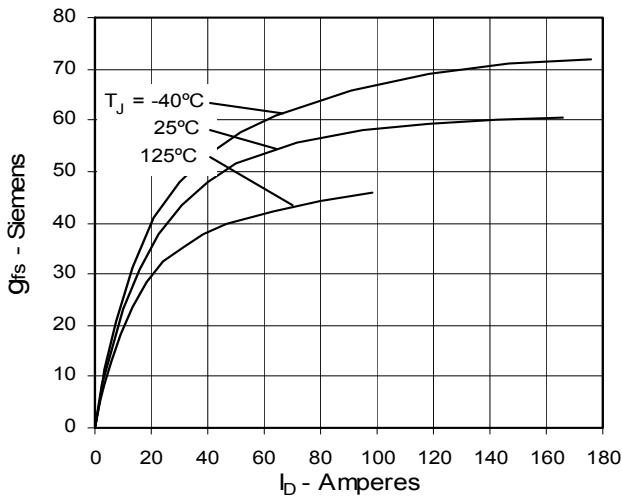
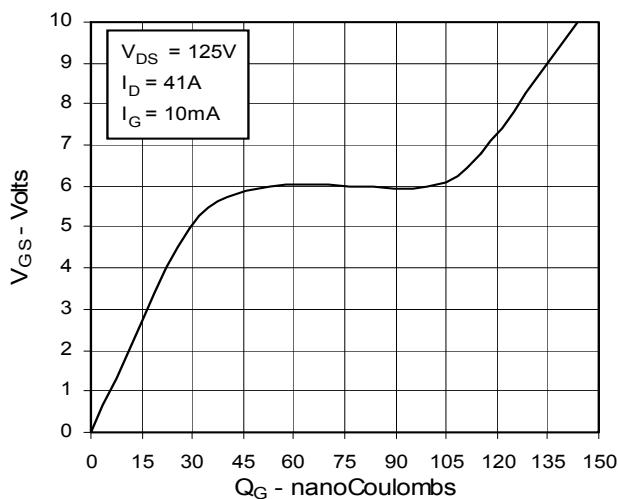
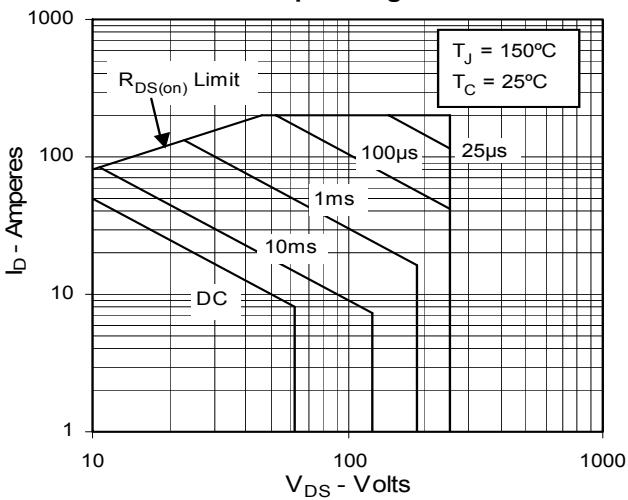
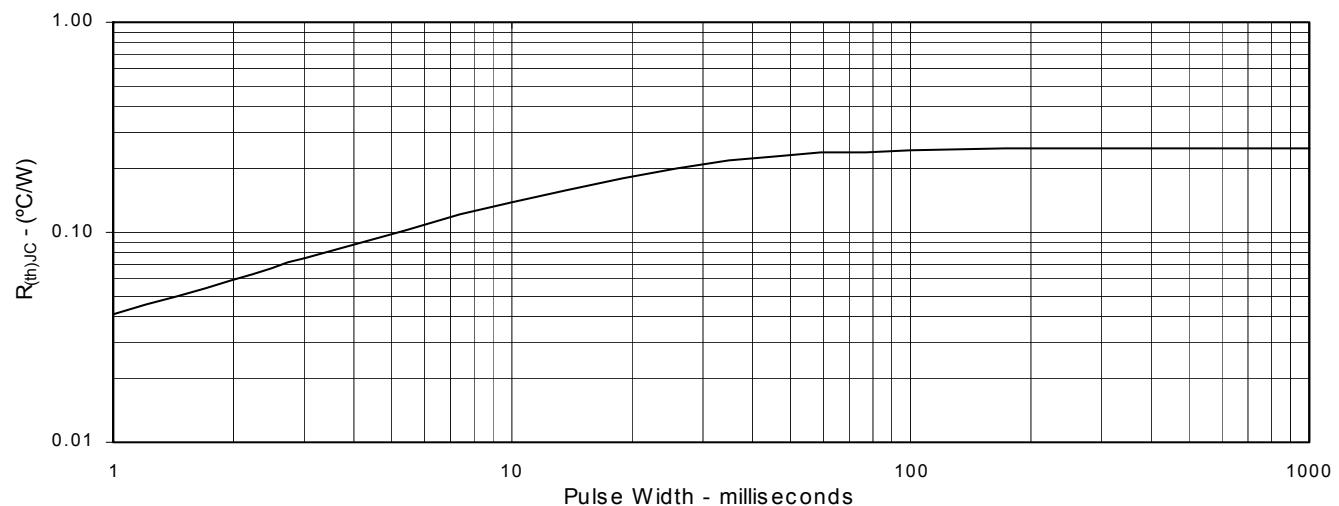
Fig. 7. Input Admittance

**Fig. 9. Source Current vs.
Source-To-Drain Voltage**

Fig. 11. Capacitance

Fig. 8. Transconductance

Fig. 10. Gate Charge

**Fig. 12. Forward-Bias
Safe Operating Area**


Fig. 13. Maximum Transient Thermal Resistance

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